

Amendments to the Abstract

Please replace the subtitle and text of the Abstract as follows:

Abstract of the Disclosure

Methods for the production of silicon nitride films by vapor-phase growth. A hydrazine gas and at least one precursor gas are fed into a reaction chamber containing a substrate. The precursor gas is either a trisilylamine gas or a silylhydrazine gas. A silicon nitride film is formed through the reaction of the hydrazine gas and the precursor gas.

Attachment: Replacement Sheet